

Supplementary materials

Stability and comparative analysis of two-dimensional AN_3 ($\text{A} = \text{Si}, \text{Sn}$) monolayers as host for K-ion storage: Insights from First-Principles calculations

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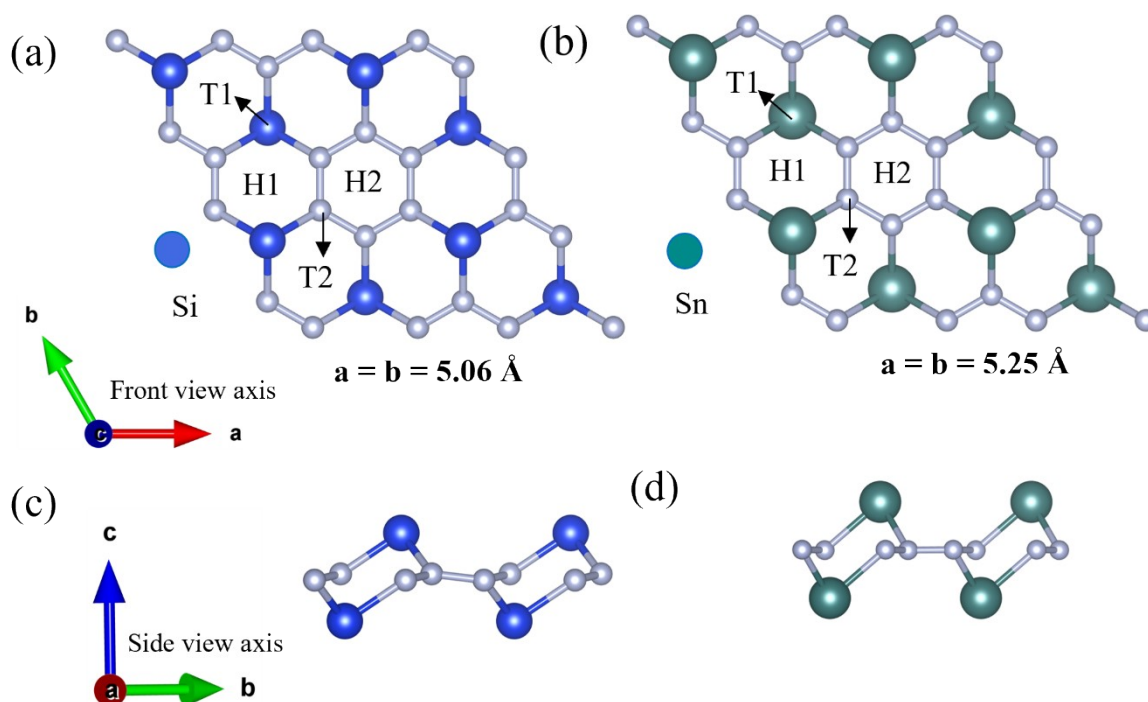


Fig. 1. Side and front view of the optimised SiN_3 and SnN_3 monolayers with selected sites for adsorption of K atom.

Table 1. the optimised 2×2 supercell structural lattice parameters of the XN_3 ($\text{X} = \text{Si}, \text{N}$) monolayers. The symbol a represents the lattice constant, the N-N and X-N bond are the distance between N with N atoms, and between X with N atoms.

2D-Structure	a (Å)	N-N bond (Å)	X-N bond (Å)
SiN_3	5.06 Å [This work]	1.36 Å	1.89 Å
	5.06 Å ¹	1.36 Å ¹	1.89 Å ¹
	5.08 Å ²	1.38 Å ²	1.88 Å ²
SnN_3	5.25 Å [This work]	1.37 Å ³	2.09 Å ³
	5.25 Å ³		

Table 2. Cohesive energy of the pristine SiN₃ and SnN₃ monolayers with other 2D monolayers materials.

Materials	E _{coh} eV/atom	Ref.
SiN ₃	6.08	1
	6.03	4
SnN ₃	6.87	This work
GeP ₃	3.34	5
SnS	3.75	6
SnB	4.60	7
VC ₄	5.2	8
SiP ₃	5.01	9

Table 3. The phonon mode of the SiN₃ and SnN₃ monolayers, with other reported two-dimensional monolayers.

Structure	Phonon frequency (cm ⁻¹)	Ref.
SiN ₃	1169	1
SnN ₃	1386	This work 3
	1386	
SiP ₃	480	9
SbP ₃	467	10
SnP ₃	500	11
MoS ₂	473	12
SnS	320	6
Si monolayer	580	13

The phonon band dispersion curve was calculated with the DFPT method using the Phonopy code ¹⁴. The calculated phonon band spectrum of the SiN₃ and SnN₃ monolayers, shows no negative phonon mode of vibration in the entire Brillouin zone. These results verify the dynamic stability of the SiN₃ and SnN₃ monolayers and compare them with other 2D materials as illustrated in Table 3.

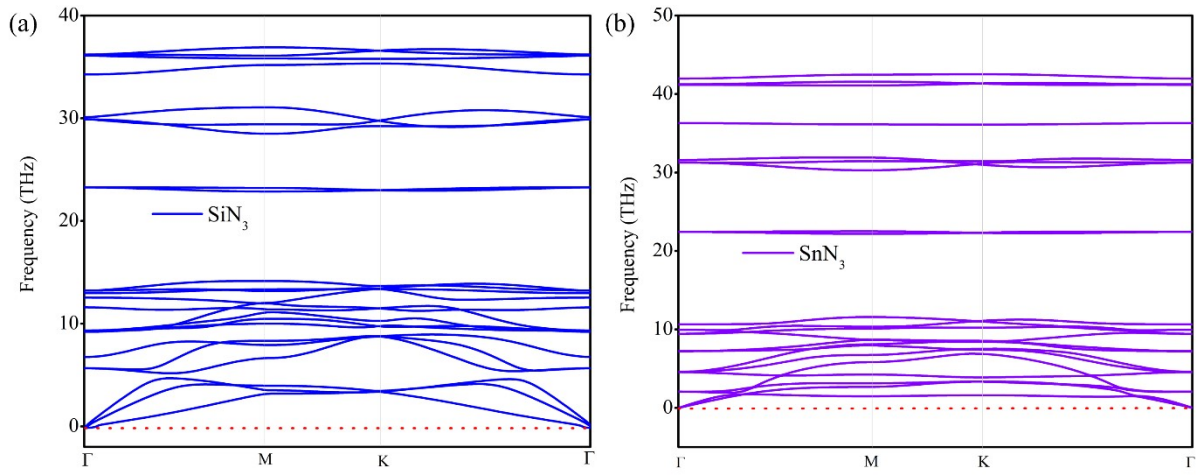


Fig. 2. Phonon band spectrum of the (a) SiN_3 and (b) SnN_3 monolayers.

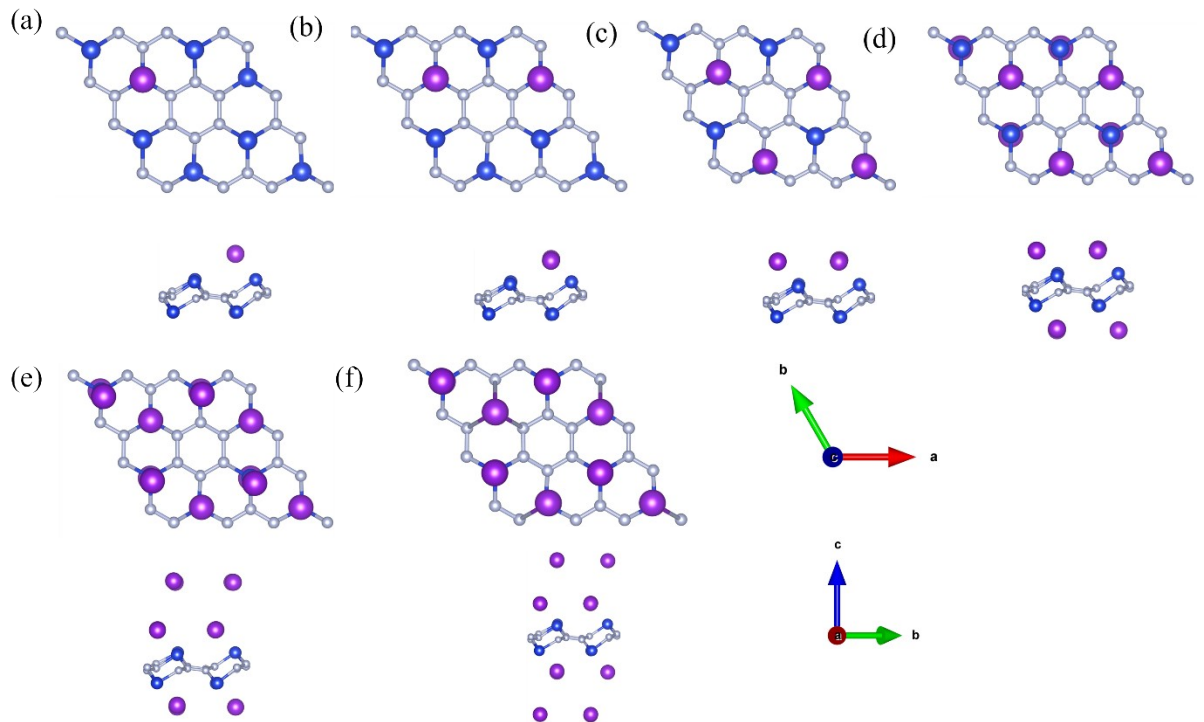


Fig. 3. Top and side views of various concentrations of potassium-ion over the SiN_3 monolayer in (a-c) single-sided and (d-f) double-sided configurations.

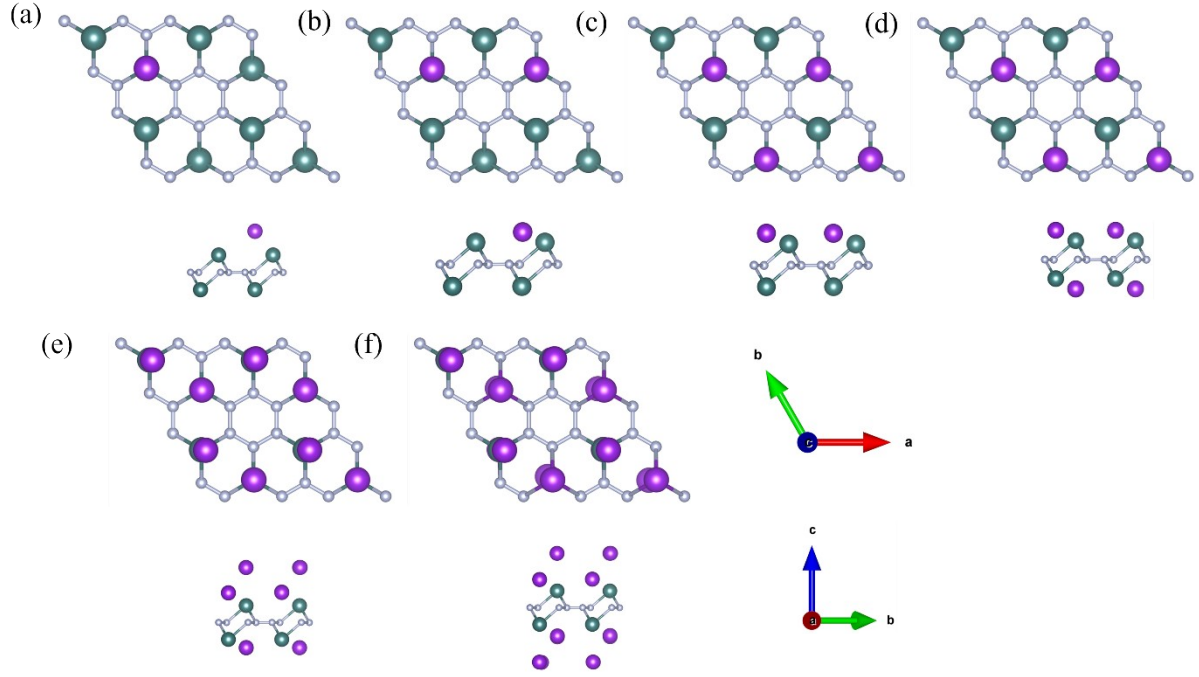


Fig. 4. Top and side views of various concentrations of potassium-ion over the SnN_3 monolayer in (a-c) single-sided and (d-f) double-sided configurations.

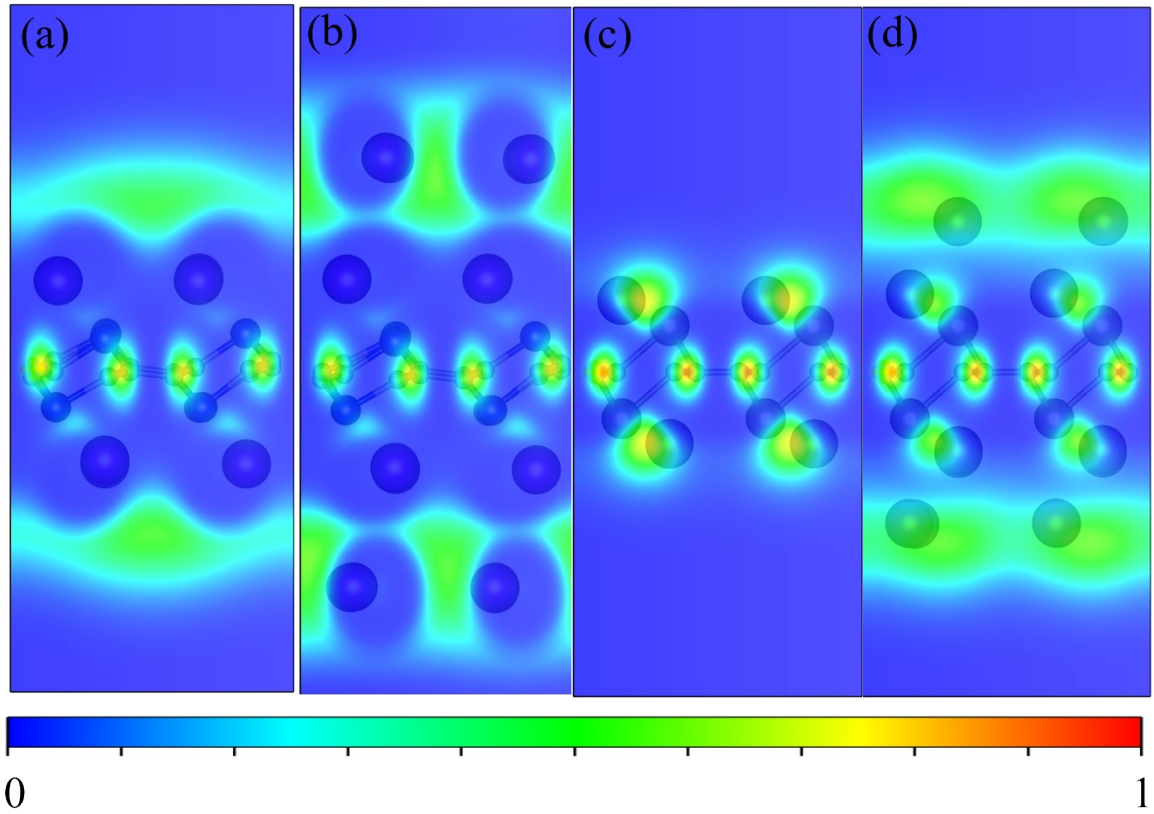


Fig. 5. Electron localisation function (ELF) map of (a) K_1SiN_3 , (b) K_2SiN_3 , (c) K_1SnN_3 and (d) K_2SnN_3 .

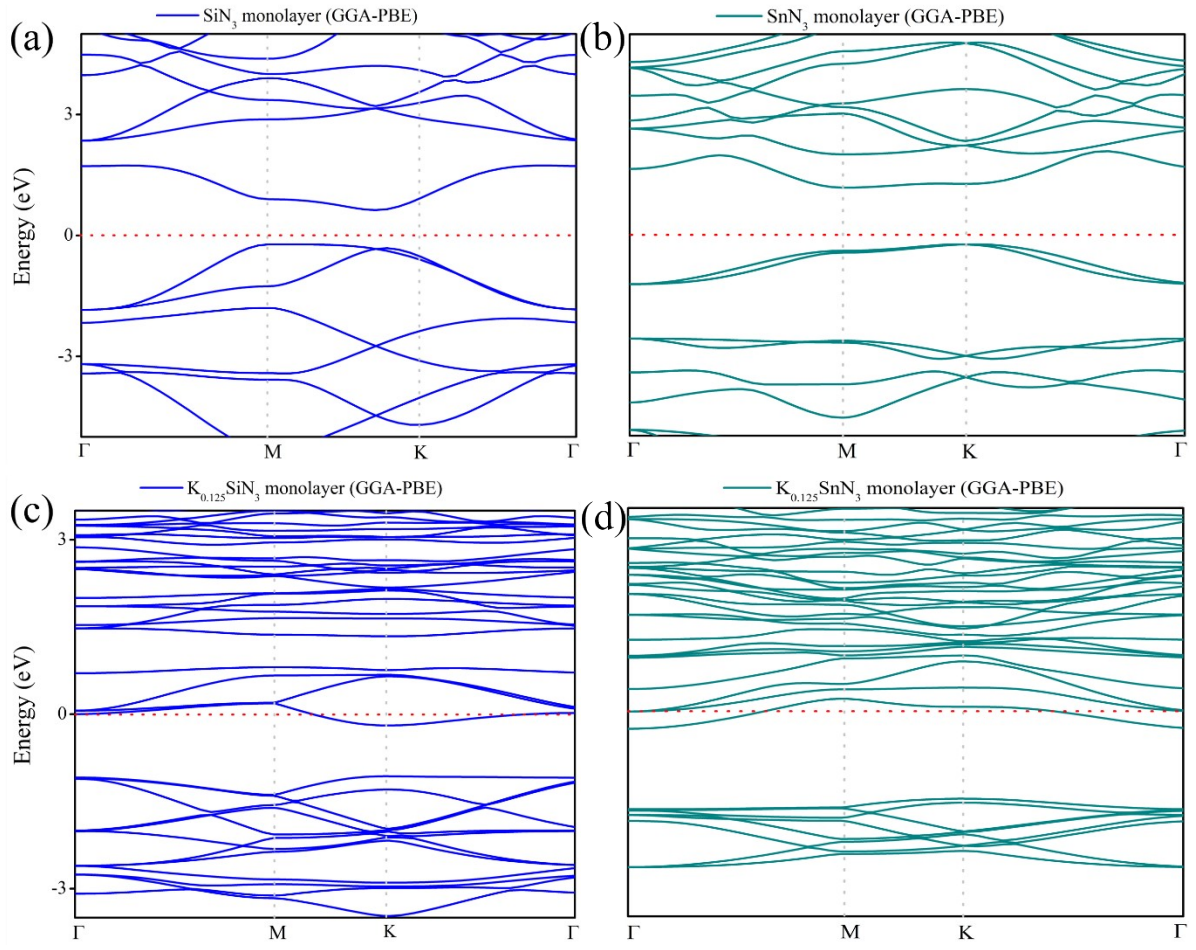


Fig. 6. Electronic band structure of the pristine (a) SiN_3 and (b) SnN_3 monolayers, and K-adsorbed (c) $\text{K}_{0.125}\text{SiN}_3$ and (d) $\text{K}_{0.125}\text{SnN}_3$ monolayers, calculated using the GGA-PBE method.

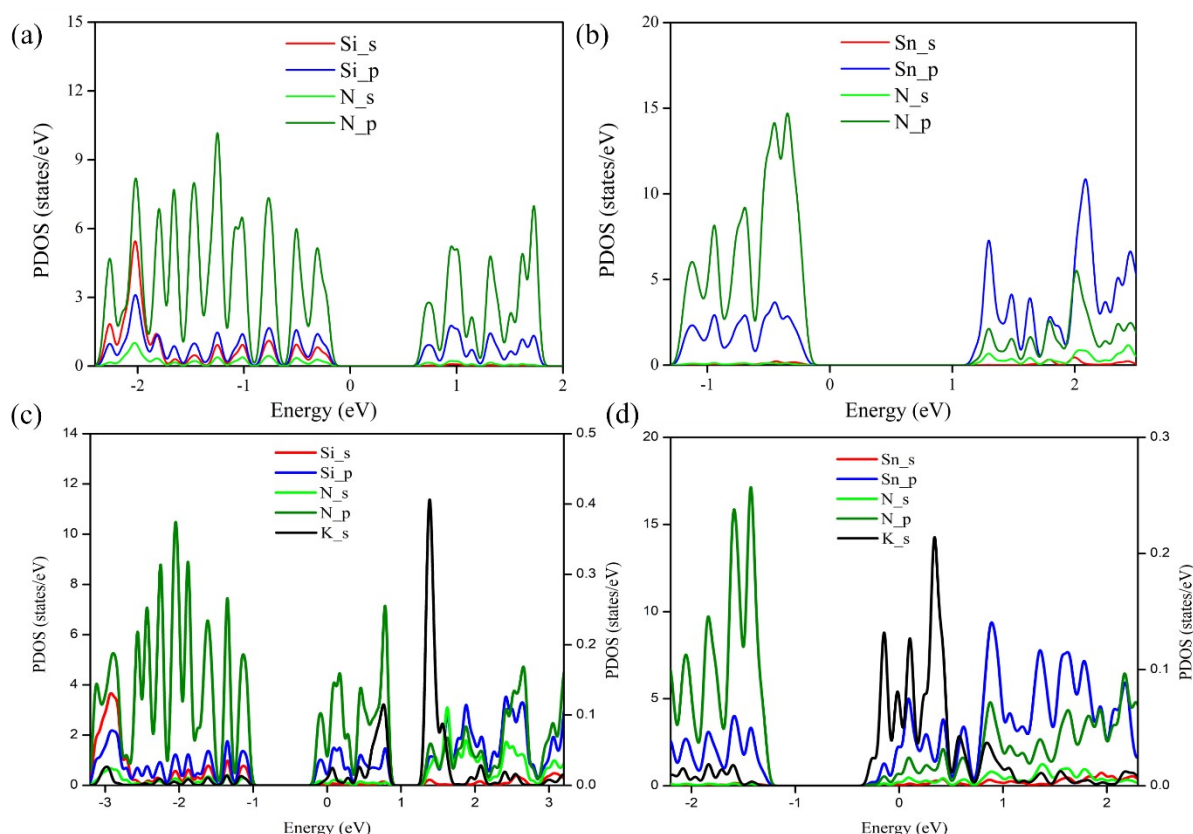


Fig. 7. Partial density of states (PDOS) of the pristine and KSiN₃ and KSnN₃ monolayers.

References

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